

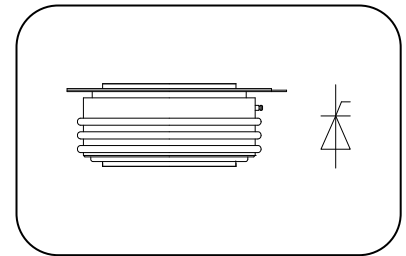
### Features:

- Int erdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses
- Short turn-off time
- Hermetic metal cases with ceramic insulators

### Typical Applications

- Ind uctive heating
- E lectronic welders
- S elf-commutated inverters
- AC motor speed control
- General power switching applications

$I_{T(AV)}$       **1010A**  
 $V_{DRM}/V_{RRM}$     **1200~1600V**  
 $t_q$                 **18~36μs**  
 $I_{TSM}$              **11kA**



SYMBOL CHAR	ACTERISTIC	TEST CONDITIONS	T <sub>j</sub> (°C)	VALUE			UNIT
				Min T	ype	Max	
I <sub>T(AV)</sub> Mean	on-state current	180° half sine wave 50Hz Double side cooled,	T <sub>C</sub> =55°C			1010	A
			T <sub>C</sub> =85°C			700	
			old model			600	
V <sub>DRM</sub> V <sub>RRM</sub>	Repetitive peak off-state voltage Repetitive peak reverse voltage	V <sub>DRM</sub> &V <sub>RRM</sub> ,tp=10ms V <sub>DSM</sub> &V <sub>RSM</sub> = V <sub>DRM</sub> &V <sub>RRM</sub> +100V	125	1200		1600	V
I <sub>DRM</sub> I <sub>RRM</sub>	Repetitive peak off-state current Repetitive peak reverse current	V <sub>D</sub> = V <sub>DRM</sub> V <sub>R</sub> = V <sub>RRM</sub>	125			50	mA
I <sub>TSM</sub> S	urge on-state current	10ms half sine wave	125			11	kA
I <sup>2</sup> t I	<sup>2</sup> T for fusing coordination	V <sub>R</sub> =0.6V <sub>RRM</sub>				605	A <sup>2</sup> s*10 <sup>3</sup>
V <sub>TO</sub> Th	reshold voltage		125			1.70	V
r <sub>T</sub>	On-state slop resistance					0.48	mΩ
V <sub>TM</sub> P	peak on-state voltage	I <sub>TM</sub> =1800A, F=21kN	125			2.56	V
dv/dt	Critical rate of rise of off-state voltage	V <sub>DM</sub> =0.67V <sub>DRM</sub> 125				200	V/μs
di/dt	Critical rate of rise of on-state current	V <sub>DM</sub> = 67%V <sub>DRM</sub> t o 1600A, Gate pulse t <sub>r</sub> ≤0.5μs I <sub>GM</sub> =1.5A	125			1500	A/μs
Q <sub>rr</sub> R	ecovery charge	I <sub>TM</sub> =1000A, tp=2000μs, di/dt=-60A/μs, V <sub>R</sub> =50V	125	83		100	μC
t <sub>q</sub>	Circuit commutated turn-off time	I <sub>TM</sub> =800A, tp=1000μs, V <sub>R</sub> =50V dv/dt=30V/μs , di/dt=-20A/μs	125	18		36	μs
I <sub>GT</sub>	Gate trigger current			30		250	mA
V <sub>GT</sub> Gate	trigger voltage	V <sub>A</sub> =12V, I <sub>A</sub> =1A 25		0.8		3.0	V
I <sub>H</sub> H	olding current			20		400	mA
V <sub>GD</sub> N	on-trigger gate voltage	V <sub>DM</sub> =67%V <sub>DRM</sub> 125		0.3			V
R <sub>th(j-c)</sub>	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 21kN				0.024	°C /W
R <sub>th(c-h)</sub>	Thermal resistance case to heat sink					0.006	
F <sub>m</sub> Moun	ting force			18		25	kN
T <sub>slg</sub> S	tored temperature			-40		140	°C
W <sub>t</sub> We	ight					3800	g
Outline	KT44cT						

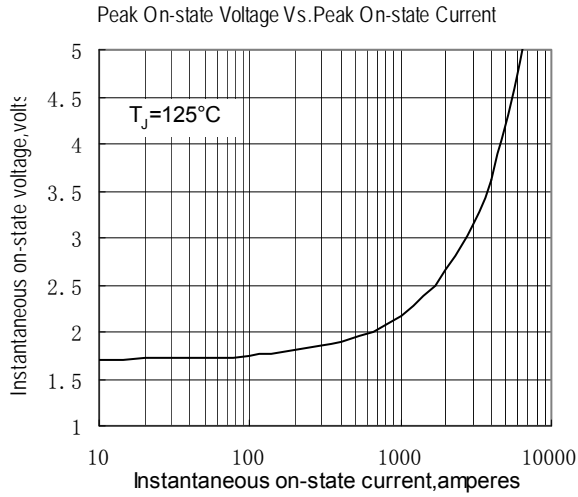


Fig.1

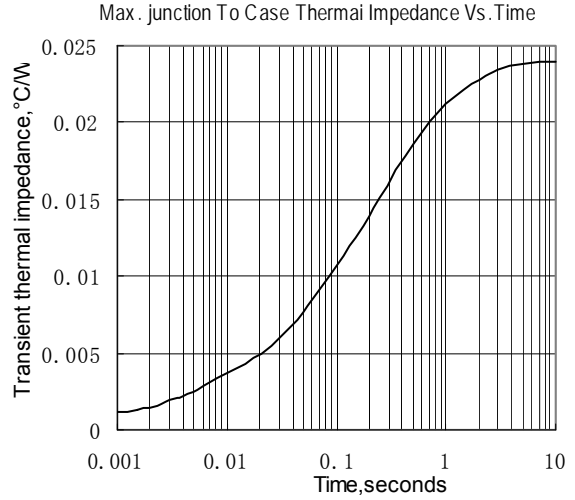


Fig.2

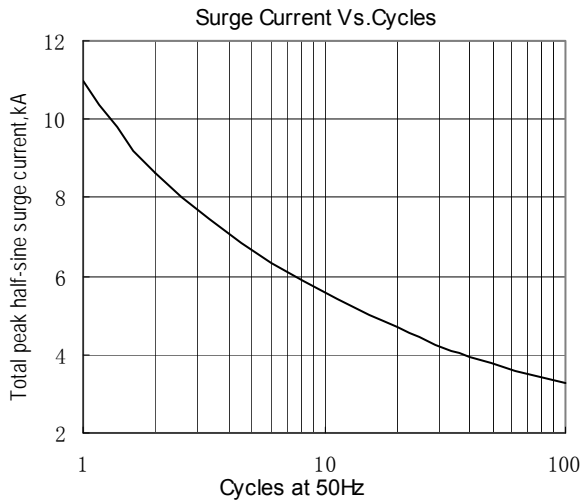


Fig.3

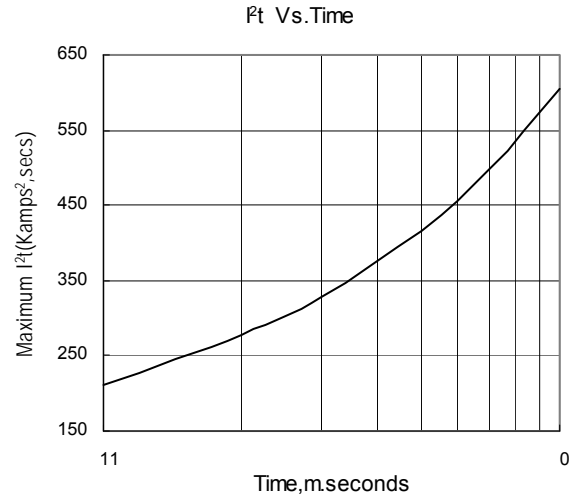


Fig.4

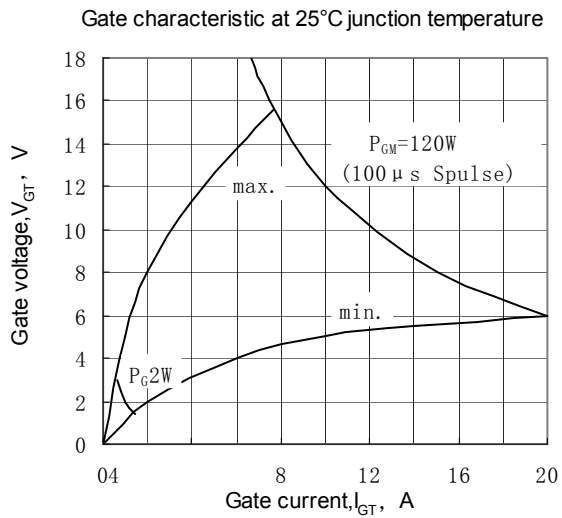


Fig.5

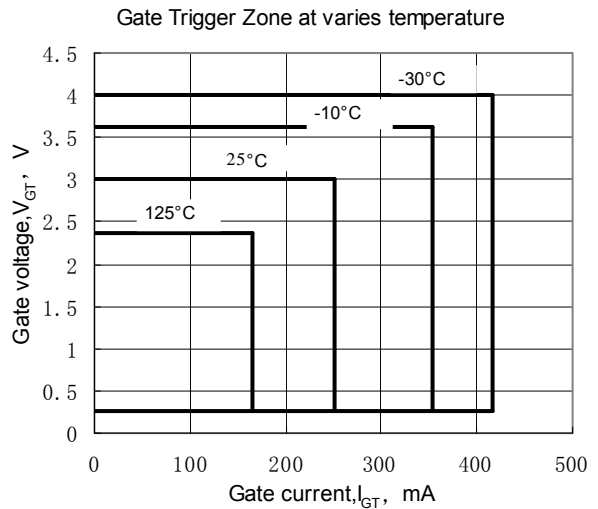


Fig.6

Outline:

